

JMSL10380PD
Features

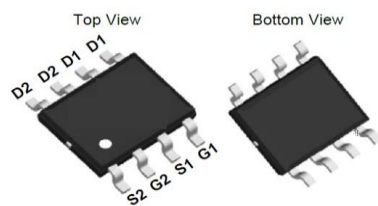
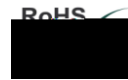
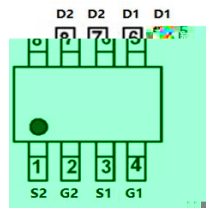
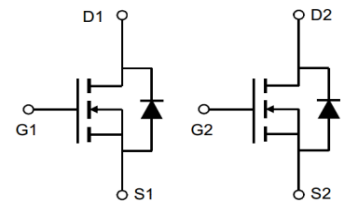
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	100	V
$V_{GS(th)}_{Typ}$	1.7	V
$I_D(@V_{GS}=10V)$	4.5	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	28	m Ω
$R_{DS(ON)}_{Typ}(@V_{GS}=4.5V)$	36	m Ω


SOP-8L-Dual

Pin Assignment

Schematic Diagram
Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSL10380PD-13	L10380PD	3	Tape&Reel	SOP-8	4000	48000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	A
		$T_A = 100^\circ\text{C}$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	26	mJ
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	W
		$T_A = 100^\circ\text{C}$	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient ⁽³⁾	88.9	$^\circ\text{C/W}$



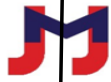
Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.7	2.5	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 20A	-	28	36	mΩ
		V _{GS} = 4.5V, I _D = 15A	-	36	47	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	1.2	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	-	536	724	pF
C _{oss}	Output Capacitance		-	176	237	pF
C _{rss}	Reverse Transfer Capacitance		-	10	50	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 20A	-	10	-	nC
Q _{gs}	Gate Source Charge		-	2.3	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	2.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 20A, R _{GEN} =3	-	5.0	-	ns
t _r	Turn-On Rise Time		-	15	-	ns
t _{d(off)}	Turn-Off DelayTime		-	12	-	ns
t _f	Turn-Off Fall Time		-	3	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	4.5	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	18	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 20A, di/dt = 100A/us	15	29	44	ns
Qrr	Body Diode Reverse Recovery Charge		-	27	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 4.2\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. R is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.

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Typical Performance Characteristics

Figure 1: Power De-rating

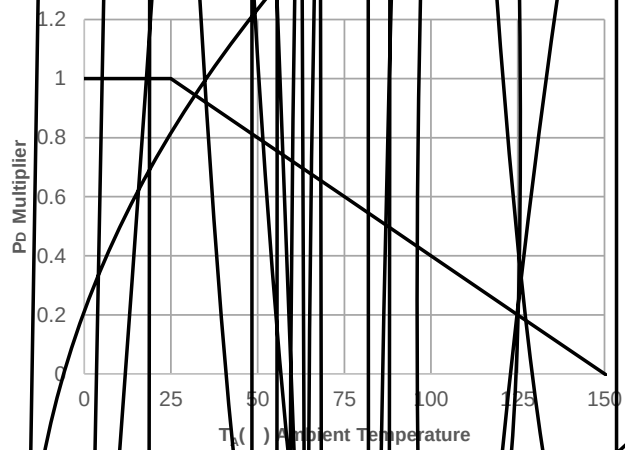
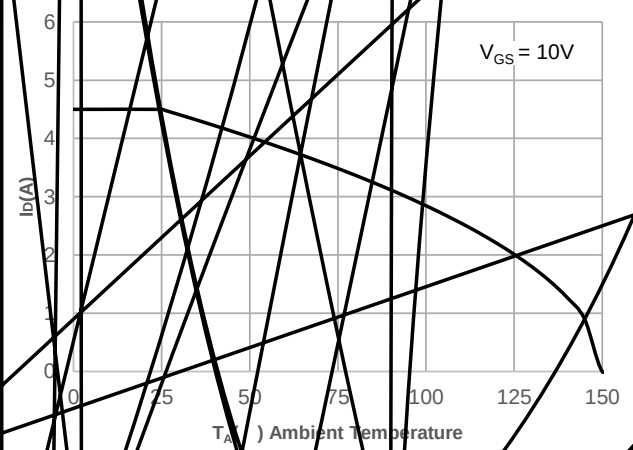
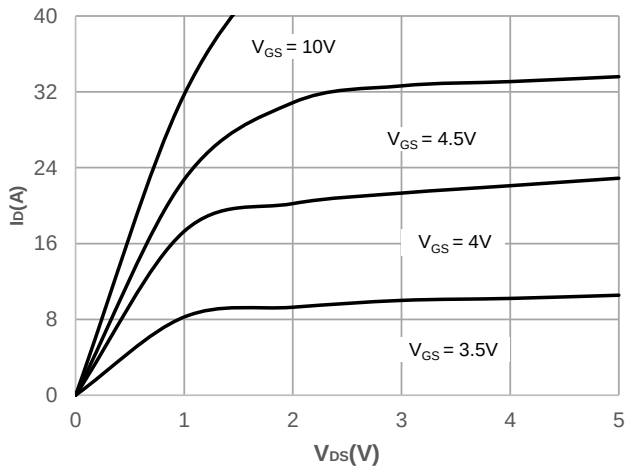
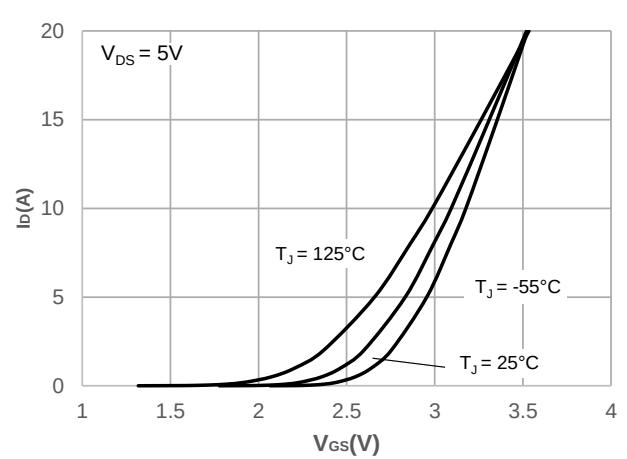
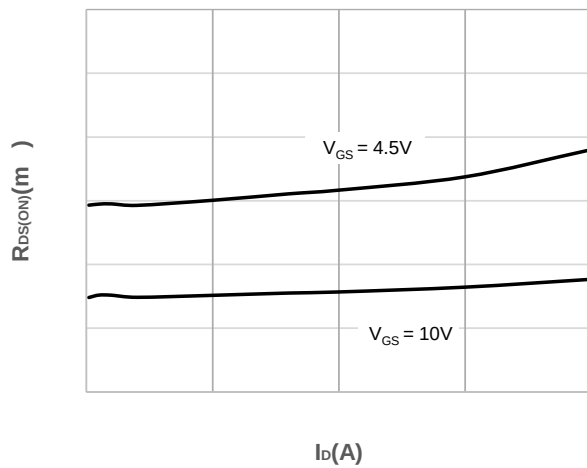
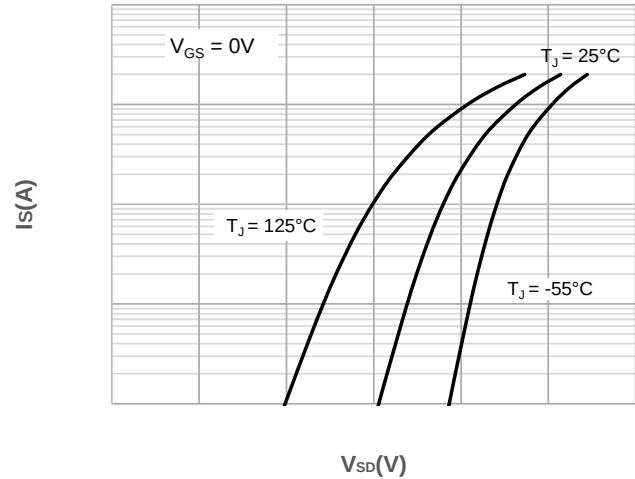
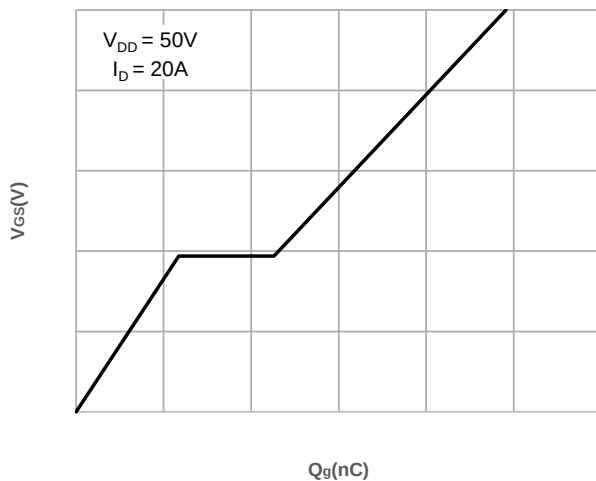
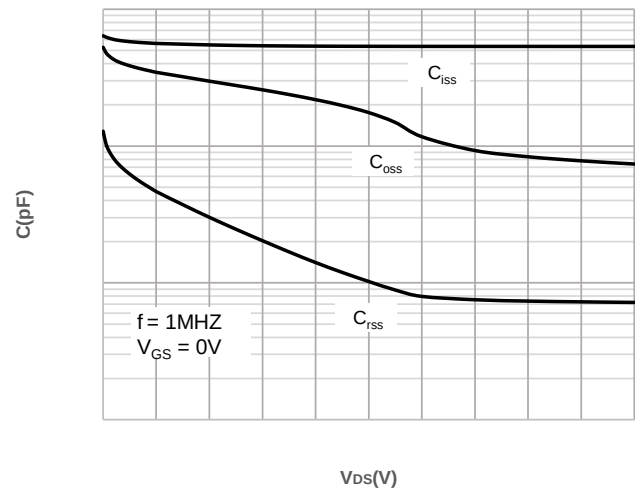


Figure 2: Current De-rating



Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

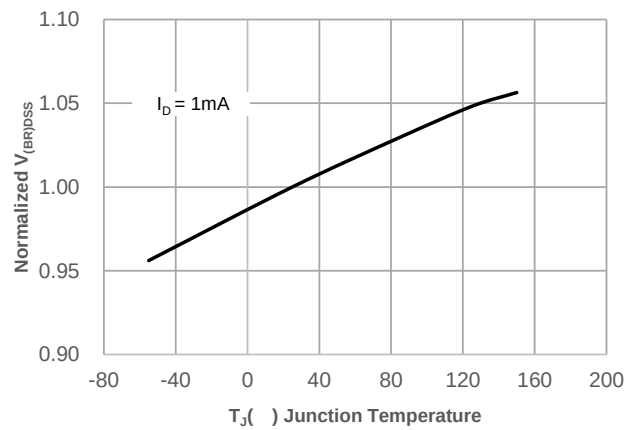
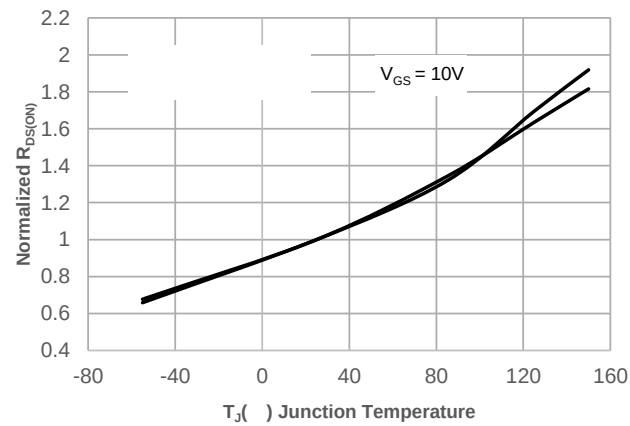


Figure 12: Normalized on Resistance vs. Junction Temperature



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

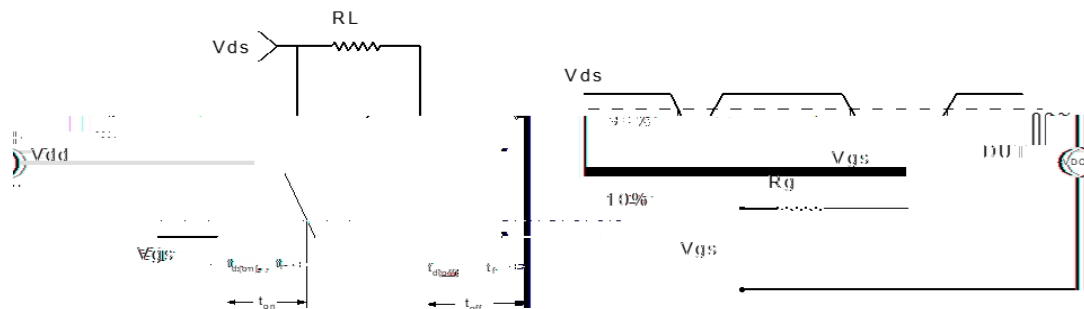


Figure 2: Resistive Switching Test Circuit & Waveform

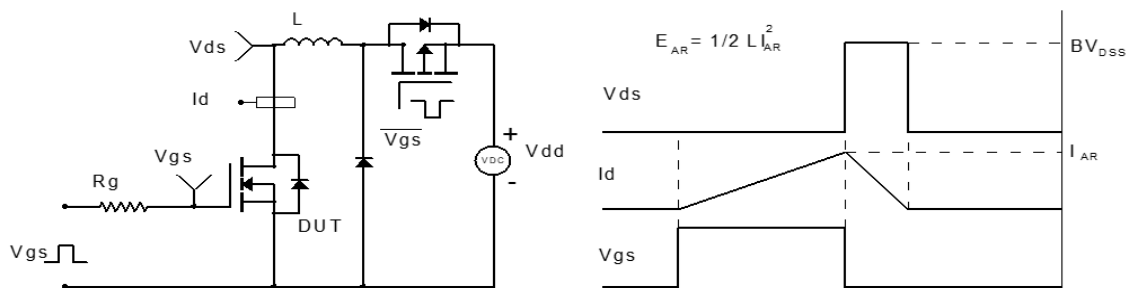


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

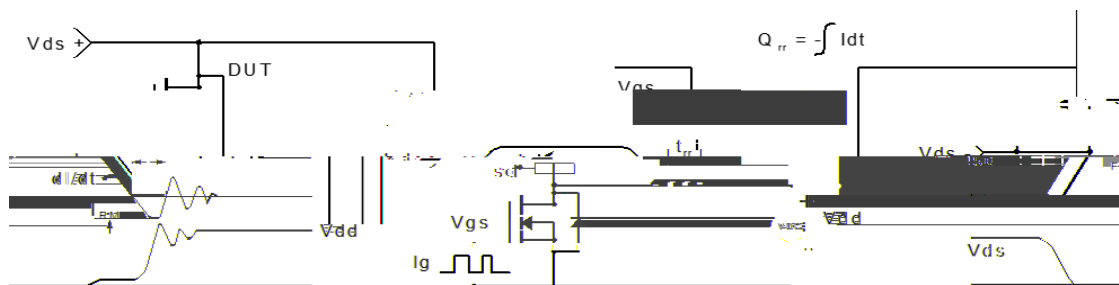
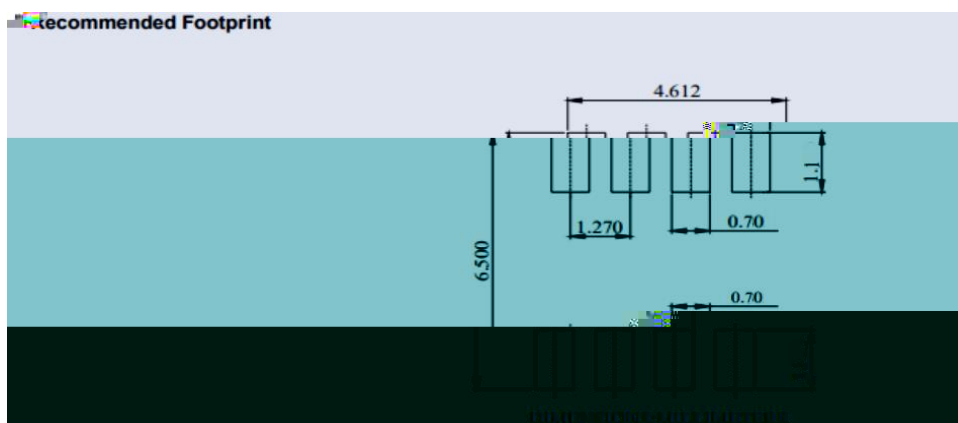
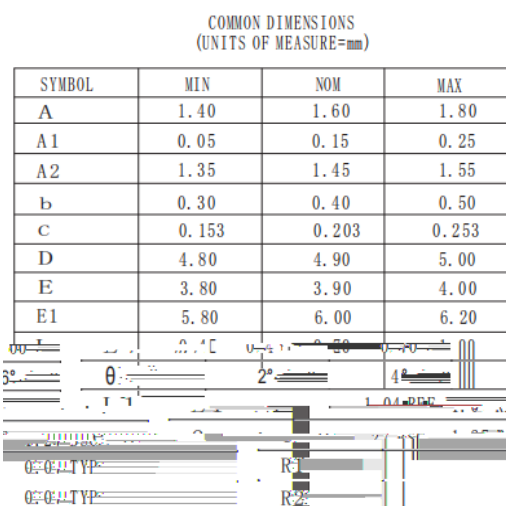


Figure 4: Diode Recovery Test Circuit & Waveform

Package Outline



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